



# PMV27UPE

20 V, P-channel Trench MOSFET

15 May 2014

Product data sheet

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability:  $P_{tot} = 980 \text{ mW}$
- ElectroStatic Discharge (ESD) protection 2 kV HBM

## 3. Applications

- LED driver
- Power management
- High-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                        | Parameter                        | Conditions   | Min | Typ | Max  | Unit       |
|-------------------------------|----------------------------------|--|-----|-----|------|------------|
| $V_{DS}$                      | drain-source voltage             | $T_j = 25 \text{ }^\circ\text{C}$  | -   | -   | -20  | V          |
| $V_{GS}$                      | gate-source voltage              |  | -8  | -   | 8    | V          |
| $I_D$                         | drain current                    | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}; t \leq 5 \text{ s}$ | [1] | -   | -5.6 | A          |
| <b>Static characteristics</b> |                                  |  |     |     |      |            |
| $R_{DSon}$                    | drain-source on-state resistance | $V_{GS} = -4.5 \text{ V}; I_D = -4.5 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$   | -   | 27  | 32   | m $\Omega$ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

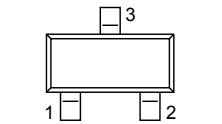
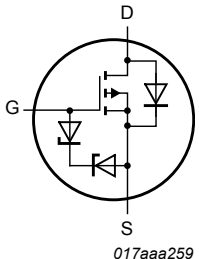


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## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline  | Graphic symbol   |
|-----|--------|-------------|---|--|
| 1   | G      | gate        |  <p>TO-236AB (SOT23)</p> |  <p>017aaa259</p> |
| 2   | S      | source      |   |  |
| 3   | D      | drain       |   |  |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |
|-------------|----------|--|---------|
|             | Name     | Description                              | Version |
| PMV27UPE    | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMV27UPE    | %KD          |

[1] % = placeholder for manufacturing site code

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions  |     | Min | Max  | Unit |
|-----------|-------------------------|---|-----|-----|------|------|
| $V_{DS}$  | drain-source voltage    | $T_j = 25\text{ °C}$  |     | -   | -20  | V    |
| $V_{GS}$  | gate-source voltage     |   |     | -8  | 8    | V    |
| $I_D$     | drain current           | $V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$           | [1] | -   | -5.6 | A    |
|           |                         | $V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$                              | [1] | -   | -4.5 | A    |
|           |                         | $V_{GS} = -4.5\text{ V}; T_{amb} = 100\text{ °C}$                             | [1] | -   | -2.8 | A    |
| $I_{DM}$  | peak drain current      | $T_{amb} = 25\text{ °C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$ |     | -   | -18  | A    |
| $P_{tot}$ | total power dissipation | $T_{amb} = 25\text{ °C}$  | [2] | -   | 490  | mW   |

| Symbol                    | Parameter            | Conditions               |     | Min | Max  | Unit |
|---------------------------|----------------------|--------------------------|-----|-----|------|------|
|                           |                      |                          | [1] | -   | 980  | mW   |
|                           |                      | T <sub>sp</sub> = 25 °C  |     | -   | 4150 | mW   |
| T <sub>j</sub>            | junction temperature |                          |     | -55 | 150  | °C   |
| T <sub>amb</sub>          | ambient temperature  |                          |     | -55 | 150  | °C   |
| T <sub>stg</sub>          | storage temperature  |                          |     | -65 | 150  | °C   |
| <b>Source-drain diode</b> |                      |                          |     |     |      |      |
| I <sub>s</sub>            | source current       | T <sub>amb</sub> = 25 °C | [1] | -   | -1.2 | A    |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

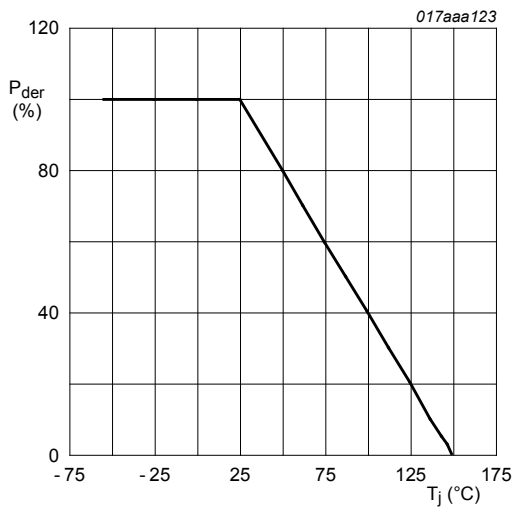


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

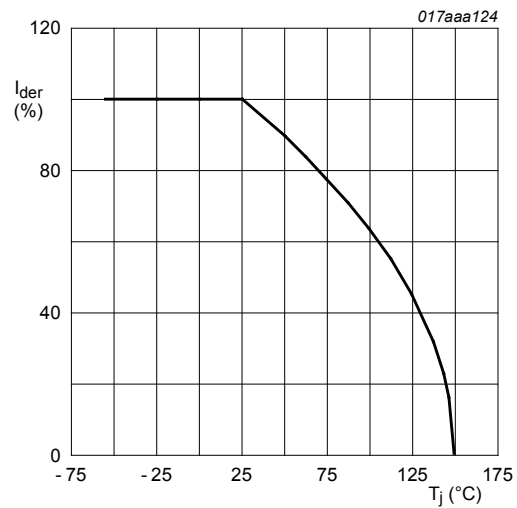
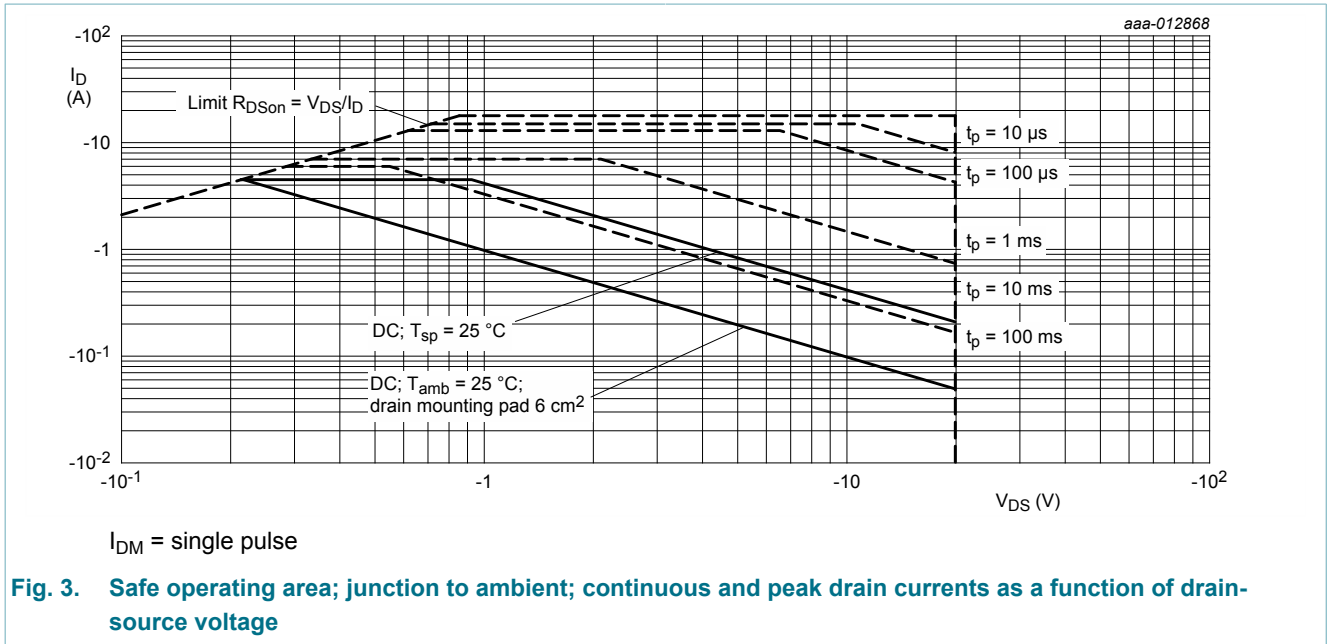


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter  | Conditions                        |     | Min | Typ | Max | Unit |
|----------------|--|-----------------------------------|-----|-----|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air                       | [1] | -   | 222 | 255 | K/W  |
|                |  |                                   | [2] | -   | 111 | 128 | K/W  |
|                |  | in free air; $t \leq 5 \text{ s}$ | [2] | -   | 74  | 85  | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |                                   |     | -   | 25  | 30  | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $6 \text{ cm}^2$ .

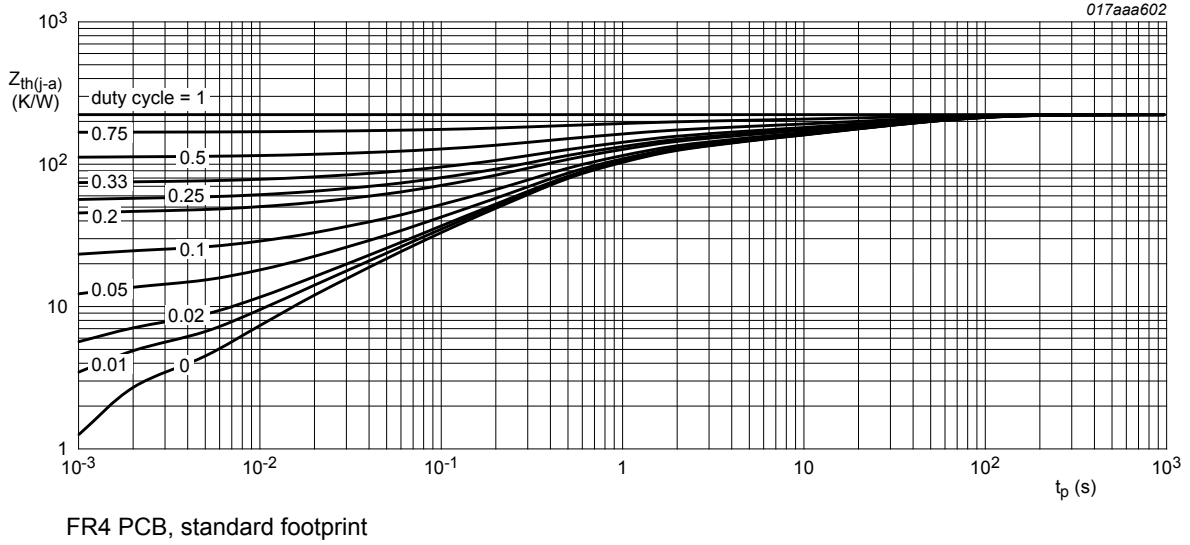


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

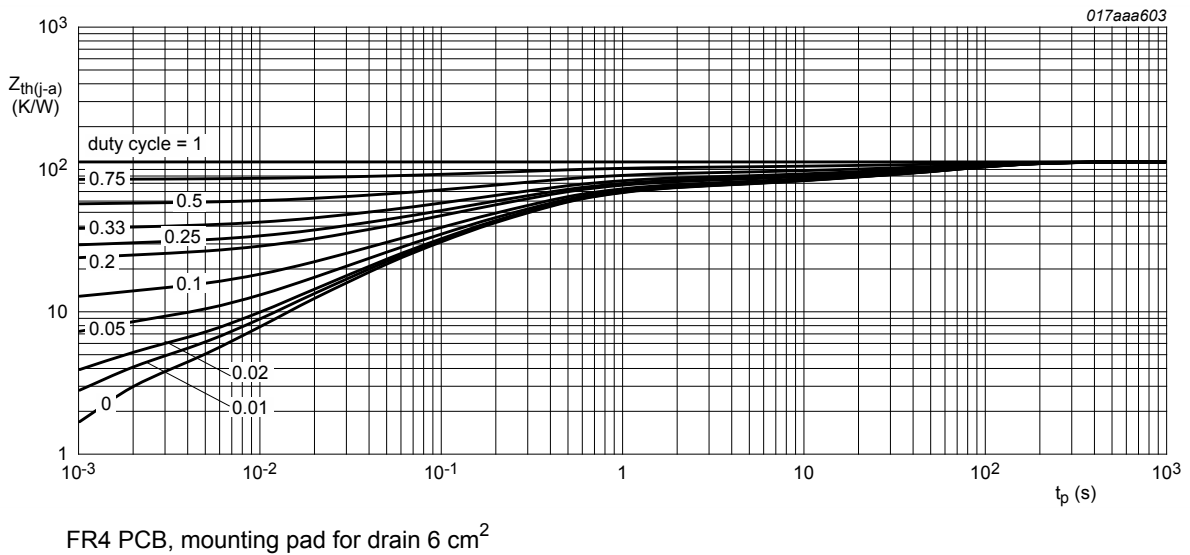
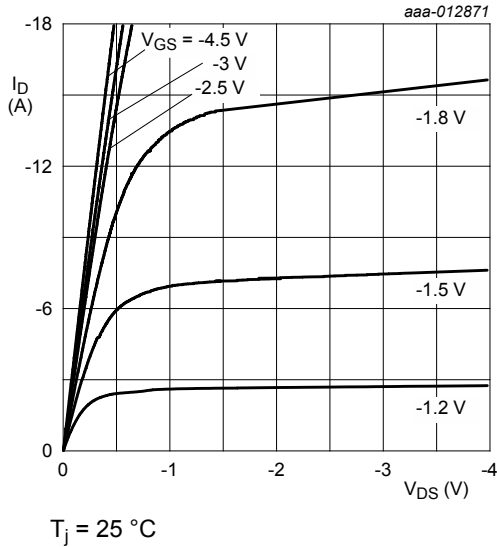


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

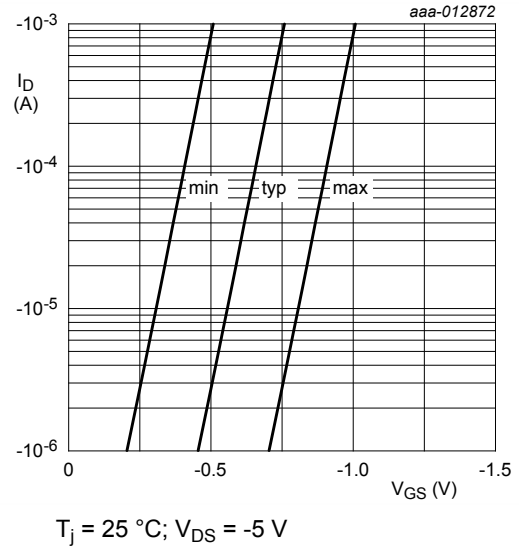
## 10. Characteristics

Table 7. Characteristics

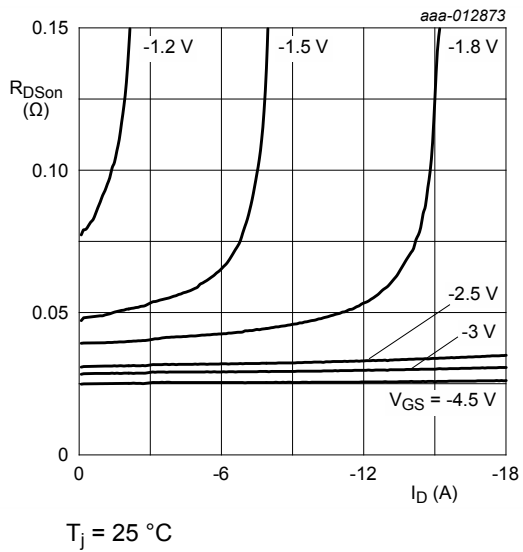
| Symbol                         | Parameter                        | Conditions  | Min   | Typ  | Max   | Unit       |
|--------------------------------|----------------------------------|---|-------|------|-------|------------|
| <b>Static characteristics</b>  |                                  |   |       |      |       |            |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage   | $I_D = -250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$   | -20   | -    | -     | V          |
| $V_{GSth}$                     | gate-source threshold voltage    | $I_D = -250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ C$  | -0.45 | -0.7 | -0.95 | V          |
| $I_{DSS}$                      | drain leakage current            | $V_{DS} = -20 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$   | -     | -    | -1    | $\mu A$    |
| $I_{GSS}$                      | gate leakage current             | $V_{GS} = 8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$   | -     | -    | 10    | $\mu A$    |
|                                |                                  | $V_{GS} = -8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$  | -     | -    | -10   | $\mu A$    |
|                                |                                  | $V_{GS} = 4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$   | -     | -    | 5     | $\mu A$    |
|                                |                                  | $V_{GS} = -4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$  | -     | -    | -5    | $\mu A$    |
| $R_{DSon}$                     | drain-source on-state resistance | $V_{GS} = -4.5 V$ ; $I_D = -4.5 A$ ; $T_j = 25 \text{ }^\circ C$  | -     | 27   | 32    | m $\Omega$ |
|                                |                                  | $V_{GS} = -4.5 V$ ; $I_D = -4.5 A$ ; $T_j = 150 \text{ }^\circ C$   | -     | 40   | 48    | m $\Omega$ |
|                                |                                  | $V_{GS} = -2.5 V$ ; $I_D = -3.8 A$ ; $T_j = 25 \text{ }^\circ C$  | -     | 38   | 45    | m $\Omega$ |
|                                |                                  | $V_{GS} = -1.8 V$ ; $I_D = -3 A$ ; $T_j = 25 \text{ }^\circ C$  | -     | 50   | 63    | m $\Omega$ |
| $g_{fs}$                       | forward transconductance         | $V_{DS} = -10 V$ ; $I_D = -2 A$ ; $T_j = 25 \text{ }^\circ C$   | -     | 15   | -     | S          |
| $R_G$                          | gate resistance                  | $f = 1 \text{ MHz}$   | -     | 10.7 | -     | $\Omega$   |
| <b>Dynamic characteristics</b> |                                  |   |       |      |       |            |
| $Q_{G(tot)}$                   | total gate charge                | $V_{DS} = -10 V$ ; $I_D = -4.4 A$ ; $V_{GS} = -4.5 V$ ; $T_j = 25 \text{ }^\circ C$                           | -     | 14.7 | 22.1  | nC         |
| $Q_{GS}$                       | gate-source charge               |   | -     | 2.6  | -     | nC         |
| $Q_{GD}$                       | gate-drain charge                |   | -     | 2.5  | -     | nC         |
| $C_{iss}$                      | input capacitance                | $V_{DS} = -10 V$ ; $f = 1 \text{ MHz}$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$                         | -     | 1820 | -     | pF         |
| $C_{oss}$                      | output capacitance               |   | -     | 208  | -     | pF         |
| $C_{riss}$                     | reverse transfer capacitance     |   | -     | 146  | -     | pF         |
| $t_{d(on)}$                    | turn-on delay time               | $V_{DS} = -10 V$ ; $I_D = -4.4 A$ ; $V_{GS} = -4.5 V$ ; $R_{G(ext)} = 6 \Omega$ ; $T_j = 25 \text{ }^\circ C$ | -     | 11   | -     | ns         |
| $t_r$                          | rise time                        |   | -     | 30   | -     | ns         |
| $t_{d(off)}$                   | turn-off delay time              |   | -     | 83   | -     | ns         |
| $t_f$                          | fall time                        |   | -     | 39   | -     | ns         |
| <b>Source-drain diode</b>      |                                  |   |       |      |       |            |
| $V_{SD}$                       | source-drain voltage             | $I_S = -1.2 A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$   | -     | -0.7 | -1.2  | V          |



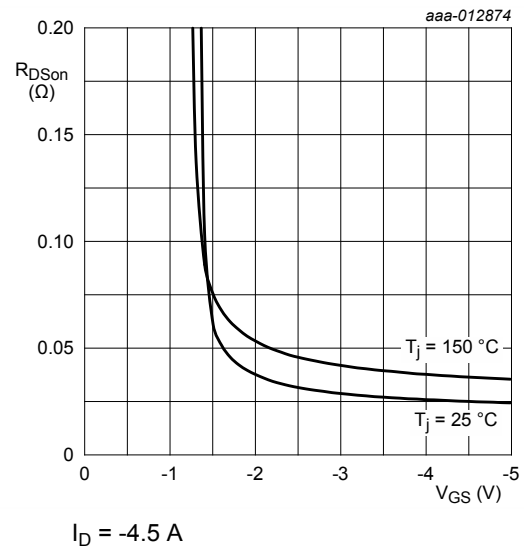
**Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



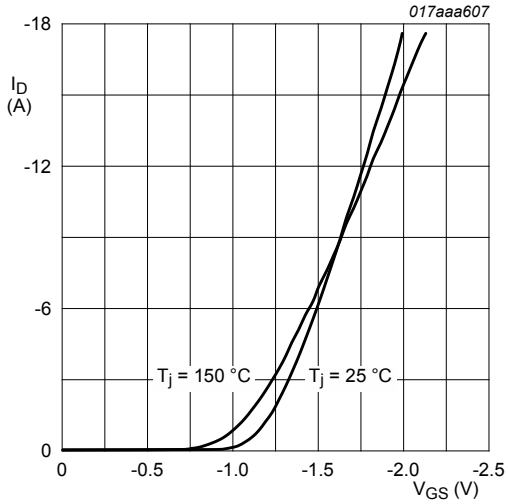
**Fig. 7. Sub-threshold drain current as a function of gate-source voltage**



**Fig. 8. Drain-source on-state resistance as a function of drain current; typical values**



**Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**



$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

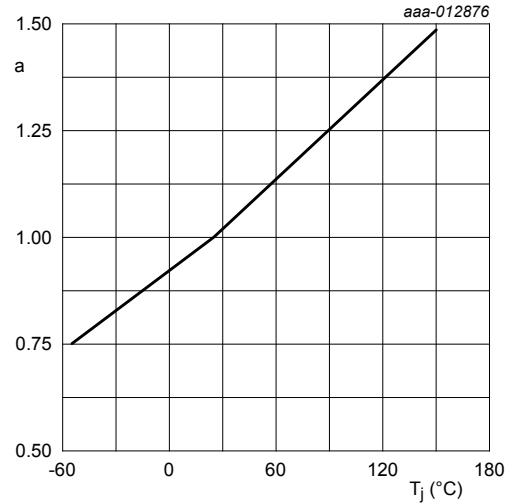
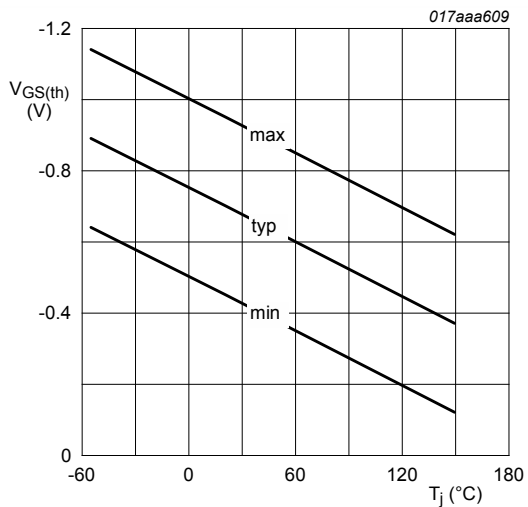


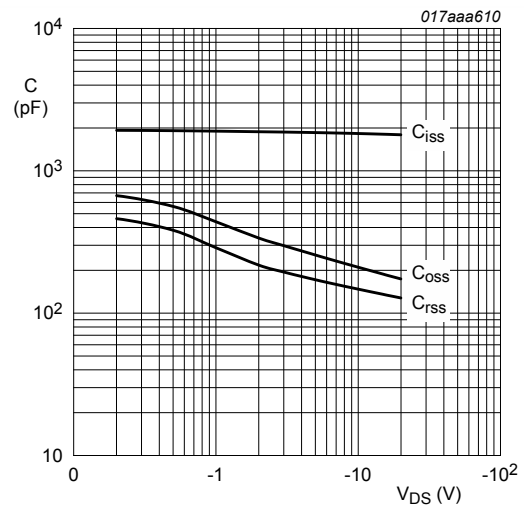
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



$$I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



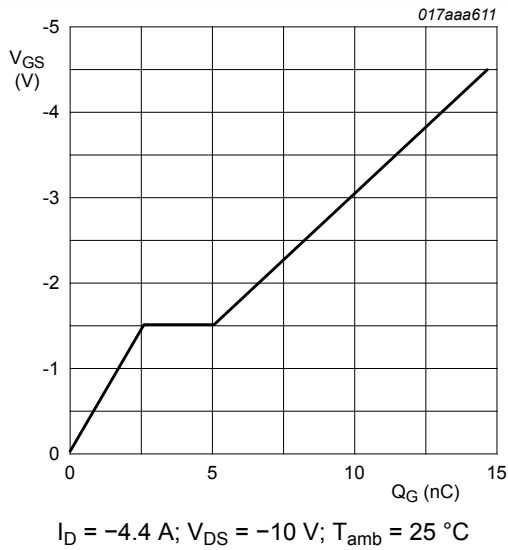


Fig. 14. Gate-source voltage as a function of gate charge; typical values

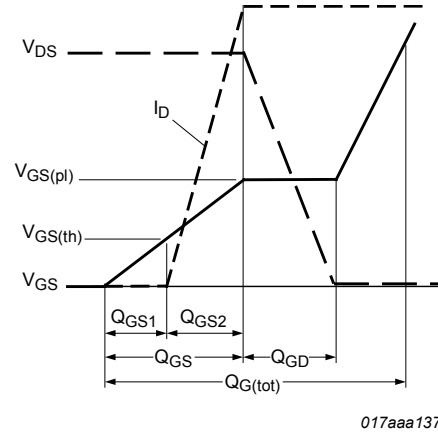


Fig. 15. MOSFET transistor: Gate charge waveform definitions

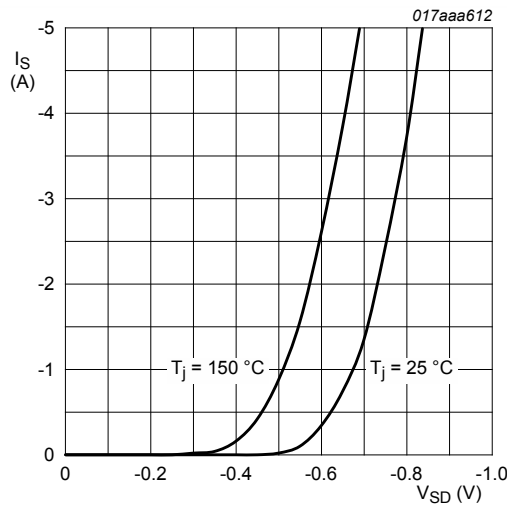


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

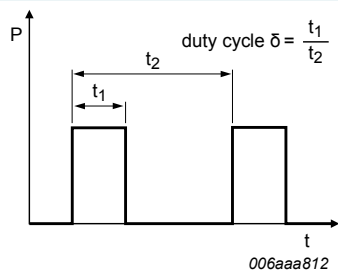


Fig. 17. Duty cycle definition

## 12. Package outline

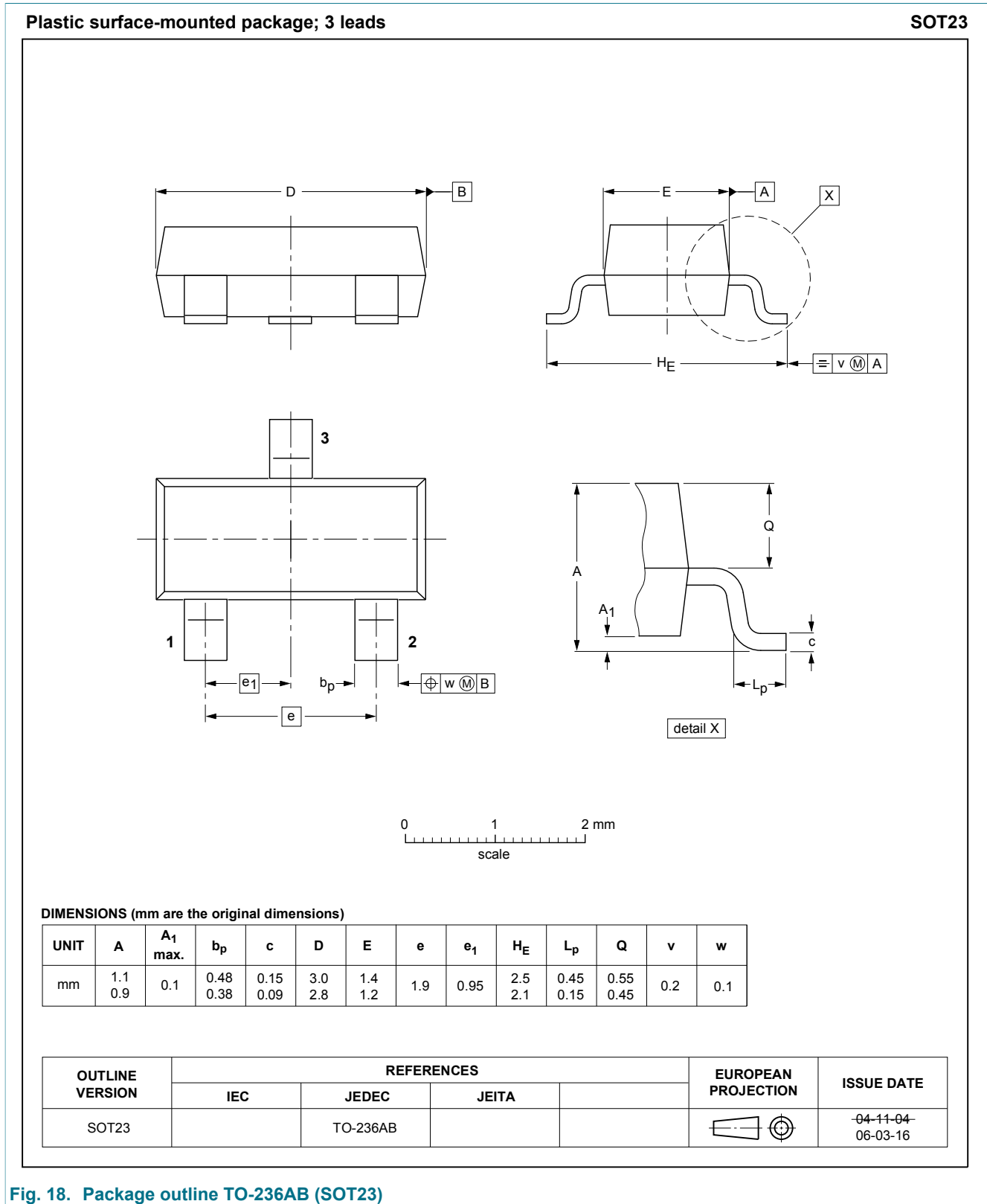


Fig. 18. Package outline TO-236AB (SOT23)

### 13. Soldering

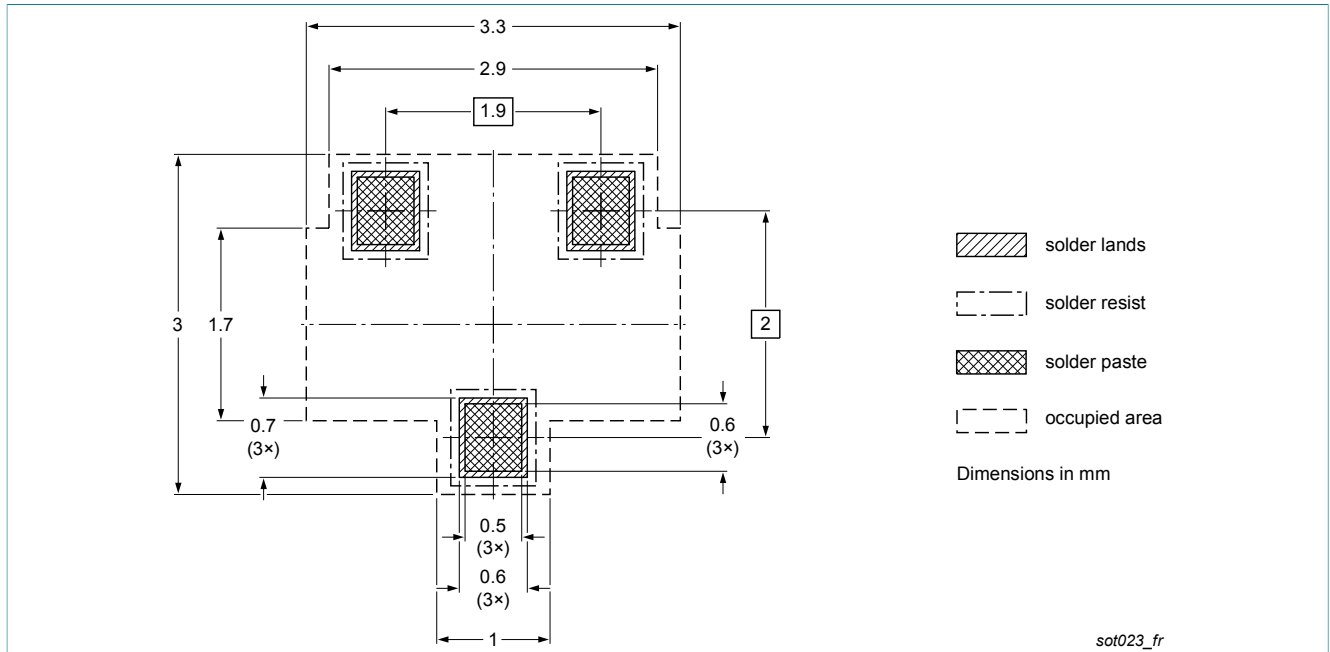


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

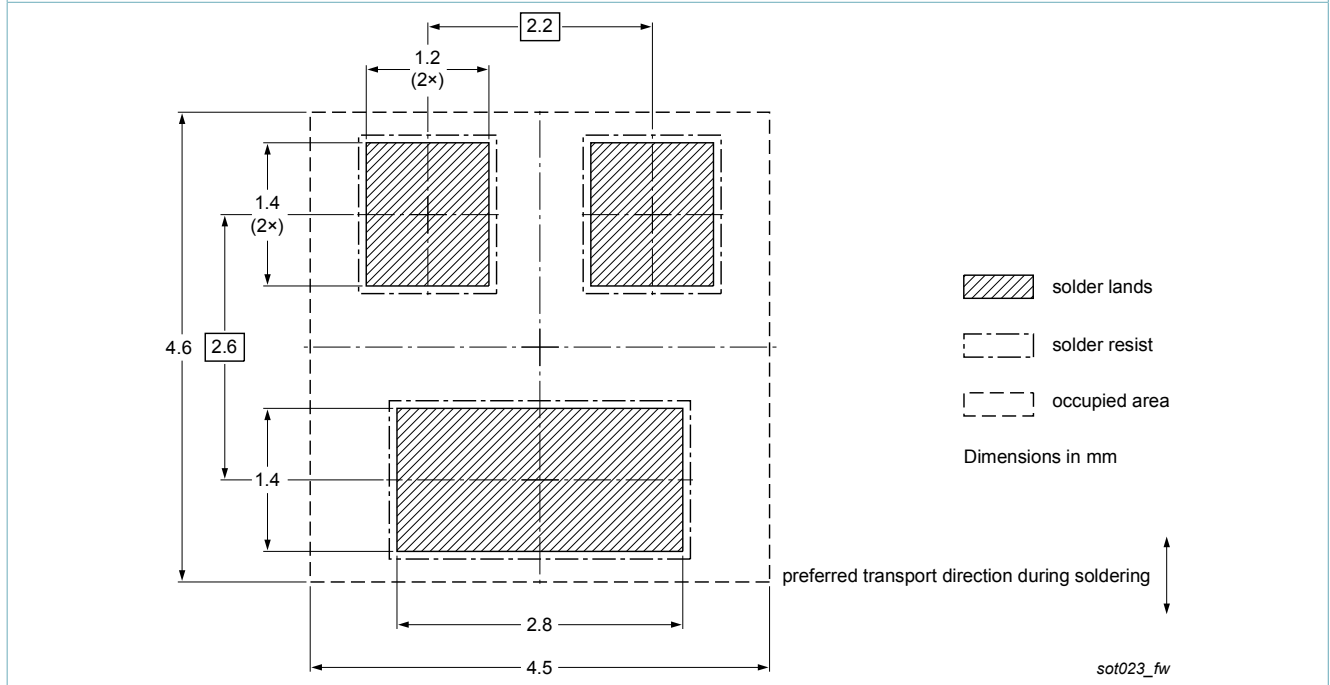


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

## 14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMV27UPE v.1  | 20140515     | Product data sheet | -             | -          |

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### 15.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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## 16. Contents

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